Preferred Device

Amplifier Transistors

NPN Silicon

Features

• These are Pb-Free Devices*

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Collector – Emitter Voltage	2N5550 2N5551	V _{CEO}	140 160	Vdc
Collector – Base Voltage	2N5550 2N5551	V _{CBO}	160 180	Vdc
Emitter – Base Voltage		V _{EBO}	6.0	Vdc
Collector Current – Continuous		I _C	600	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C		P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C		P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range		T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

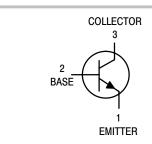
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	83.3	°C/W

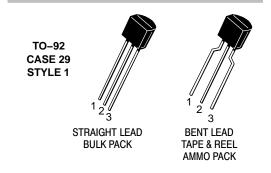
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



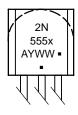
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http://onsemi.com





MARKING DIAGRAM



x = 0 or 1

A = Assembly Location

Y = Year

WW = Work Week

= Pb–Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS	1				
Collector-Emitter Breakdown Voltage (Note 1) (I _C = 1.0 mAdc, I _B = 0)	2N5550 2N5551	V _{(BR)CEO}	140 160	_ _	Vdc
Collector–Base Breakdown Voltage ($I_C = 100 \mu Adc, I_E = 0$)	2N5550 2N5551	V _{(BR)CBO}	160 180	- -	Vdc
Emitter-Base Breakdown Voltage $(I_E=10~\mu Adc,~I_C=0)$		$V_{(BR)EBO}$	6.0	-	Vdc
	2N5550 2N5551 2N5550 2N5551	Ісво	- - - -	100 50 100 50	nAdc μAdc
Emitter Cutoff Current (V _{EB} = 4.0 Vdc, I _C = 0)		I _{EBO}	_	50	nAdc
ON CHARACTERISTICS (Note 1)				-	
DC Current Gain $ (I_C = 1.0 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc}) $ $ (I_C = 10 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc}) $	2N5550 2N5551 2N5550	h _{FE}	60 80 60	- - 250	-
$(I_C = 50 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$	2N5551 2N5550 2N5551		80 20 30	250 - -	
Collector-Emitter Saturation Voltage (I _C = 10 mAdc, I _B = 1.0 mAdc) (I _C = 50 mAdc, I _B = 5.0 mAdc)	Both Types 2N5550 2N5551	V _{CE(sat)}	- - -	0.15 0.25 0.20	Vdc
Base-Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}$, $I_B = 1.0 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}$, $I_B = 5.0 \text{ mAdc}$)	Both Types 2N5550 2N5551	V _{BE(sat)}	- - -	1.0 1.2 1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I _C = 10 mAdc, V _{CE} = 10 Vdc, f = 100 MHz)		f _T	100	300	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)		C _{obo}	_	6.0	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)	2N5550 2N5551	C _{ibo}	- -	30 20	pF
Small–Signal Current Gain (I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)		h _{fe}	50	200	-
Noise Figure (I _C = 250 μ Adc, V _{CE} = 5.0 Vdc, R _S = 1.0 k Ω , f = 1.0 kHz)	2N5550 2N5551	NF	_ _	10 8.0	dB

^{1.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

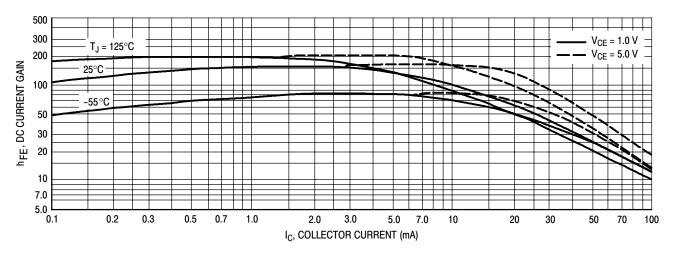


Figure 1. DC Current Gain

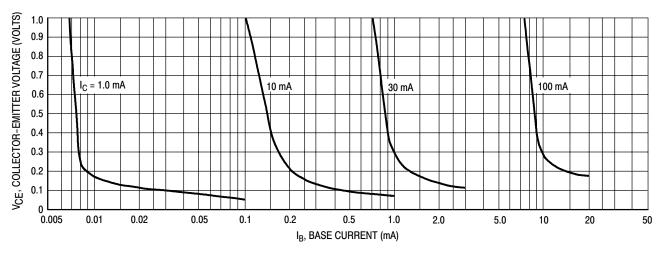


Figure 2. Collector Saturation Region

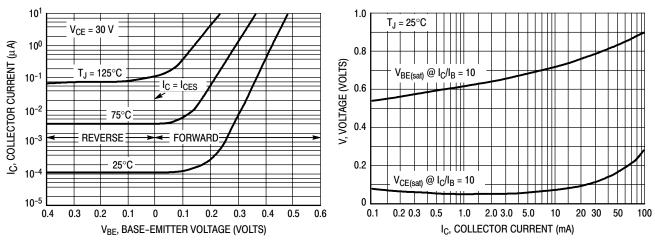


Figure 3. Collector Cut-Off Region

Figure 4. "On" Voltages

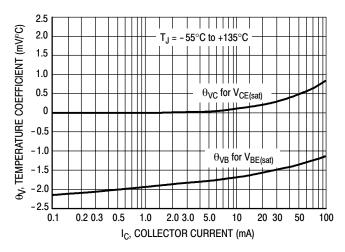
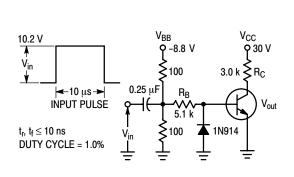


Figure 5. Temperature Coefficients



Values Shown are for $I_{\mathbb{C}} @ 10 \text{ mA}$

1000

500

300 200

100

50

30

20

10

0.2 0.3 0.5

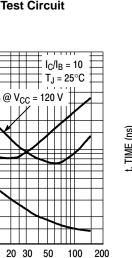
t, TIME (ns)

t_r @ V_{CC} = 30 V

 $t_d @ V_{EB(off)} = 1.0 V$

 V_{CC} = 120 V

Figure 6. Switching Time Test Circuit



I_C, COLLECTOR CURRENT (mA)

Figure 8. Turn-On Time

10

2.0 3.0 5.0

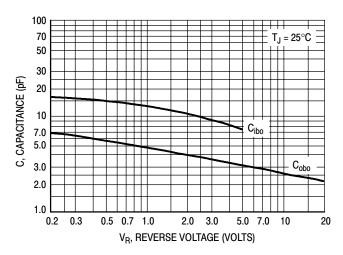


Figure 7. Capacitances

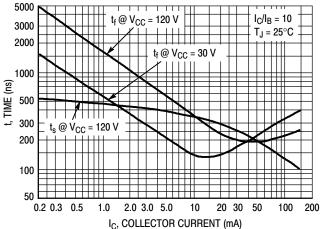


Figure 9. Turn-Off Time

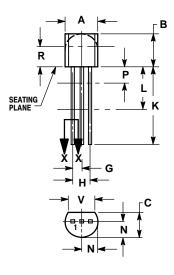
ORDERING INFORMATION

Device	Package	Shipping [†]	
2N5550G	TO-92 (Pb-Free)	5000 Units / Bulk	
2N5550RLRPG	TO-92 (Pb-Free)	2000 / Tape & Ammo Box	
2N5551G	TO-92 (Pb-Free)	5000 Units / Bulk	
2N5551RL1G	TO-92 (Pb-Free)	2000 / Tana 8 Dayl	
2N5551RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel	
2N5551RLRPG	TO-92 (Pb-Free)	- 2000 / Tape & Ammo Box	
2N55551ZL1G	TO-92 (Pb-Free)		

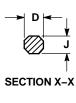
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AM**



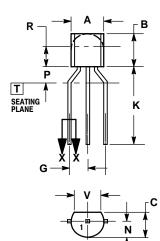
STRAIGHT LEAD **BULK PACK**



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R
 IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
V	0 135		3 43	



BENT LEAD TAPE & REEL AMMO PACK



NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS
- DIMENSION R IS UNCONTROLLED.

 LEAD DIMENSION IS UNCONTROLLED IN
- P AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.45	5.20	
В	4.32	5.33	
С	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
K	12.70		
N	2.04	2.66	
P	1.50	4.00	
R	2.93		
V	3.43		

PIN 1. EMITTER

BASE

COLLECTOR

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